Diode Semiconductor Device - Page 1 of 1



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Ind	closure Material:
Me	etal
0\	verall Length:
0.4	405 inches
Mo	ounting Facility Quantity:
1	
Jo	int Electronic Device Engineering Council/jedec/case Outline Designation:
Do	p-4
Mo	ounting Method:
Th	readed stud
Fe	atures Provided:
Mo	ounting hardware and hermetically sealed case
0\	verall Width Across Flats:
Be	tween 0.424 inches and 0.437 inches
Th	read Size:
0.1	190 inches
Se	miconductor Material:
Sil	icon
Vo	Itage Rating In Volts Per Characteristic:
30	0.0 breakdown voltage, dc
Cι	irrent Rating Per Characteristic:
2.0	00 milliamperes forward current, average peak
Ma	aximum Operating Tempurature Per Measurement Point:
15	0.0 degrees celsius ambient air
Th	read Series Designator:
Ur	ıf
Те	rminal Type And Quantity:
1 t	ab, solder lug and 1 threaded stud
Sh	nelf Life:
N/a	a
Ur	nit Of Measure:
De	emilitarization:
Nc	
Fii	g:
A1	10a0